



PSMN012-60HL

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LFAK56D using TrenchMOS technology enhanced for repetitive avalanche

30 September 2022

Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFAK56D (Dual Power-SO8) package, using application specific (ASFET) repetitive avalanche silicon technology.

2. Features and benefits

- High reliability LFAK56D package, copper-clip, solder die attach and qualified to 175 °C
- Tested to 1 Bn avalanche events
- LFAK copper clip package technology
- Copper-clip, solder die attach
- High robustness and reliability

3. Applications

- Brushless DC and Brushed DC motor control
- DC-to-DC converters
- High-performance synchronous rectification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; Fig. 2		-	-	40	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1		-	-	64	W
T _j	junction temperature			-55	-	175	°C
Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; Fig. 14		6.1	10	12.5	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 14 ; Fig. 15		-	22	28.3	mΩ
Dynamic characteristics FET1 and FET2							
Q _{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; Fig. 16 ; Fig. 17		-	7.9	-	nC
Q _{G(tot)}	total gate charge			-	22.4	-	nC
Avalanche Ruggedness FET1 and FET2							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 40 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 7	[1] [2]	-	-	82	mJ

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LPAK56D using TrenchMOS technology enhanced for repetitive avalanche

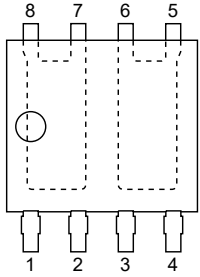
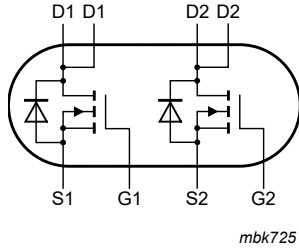
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode FET1 and FET2						
Q_r	recovered charge	$I_S = 10\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 30\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	18.9	-	nC

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 LPAK56D; Dual LPAK (SOT1205)	 mbk725
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN012-60HL	LPAK56D; Dual LPAK	plastic, single ended surface mounted package (LPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN012-60HL	12RL60H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$	-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	60	V
V_{GS}	gate-source voltage	DC; $T_j \leq 175\text{ }^\circ\text{C}$	-10	10	V
		Pulsed; $T_j \leq 175\text{ }^\circ\text{C}$	[1] [2] -15	15	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1	-	64	W

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LPAK56D using TrenchMOS technology enhanced for repetitive avalanche

Symbol	Parameter	Conditions		Min	Max	Unit
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2		-	40	A
		$V_{GS} = 5\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 2		-	33	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3		-	190	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
I_S	source current	$T_{mb} = 25\text{ °C}$		-	40	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	190	A
Avalanche ruggedness						
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	$I_D = 1.92\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 10\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(rise)} \leq 30\text{ °C}$; unclamped; Fig. 4; Fig. 5; Fig. 6	[3] [4] [5]	-	75.2	mJ
Avalanche Ruggedness FET1 and FET2						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 40\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; Fig. 7	[6] [7]	-	82	mJ

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
 [2] Significantly longer life times are achieved by lowering T_j and/or V_{GS} .
 [3] Repetitive avalanche rating is limited by maximum junction temperature of 175 °C and junction rise of 30 °C
 [4] Refer to Fig. 5 for the limiting number of avalanche events
 [5] Refer to Fig. 6 $R_{ds(on)}$ at $V_{GS}=5\text{V}$ will increase as a function of repetitive avalanche cycles
 [6] Refer to application note AN10273 for further information
 [7] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

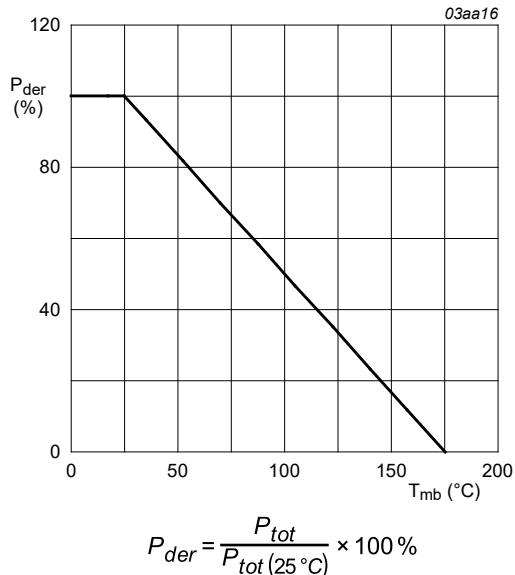


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

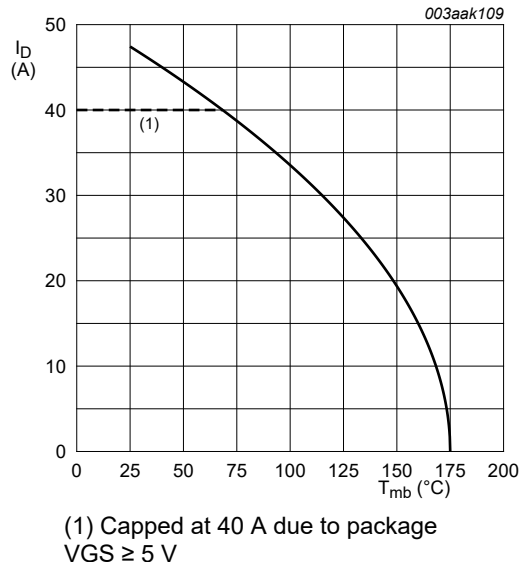


Fig. 2. Continuous drain current as a function of mounting base temperature

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LPAK56D using TrenchMOS technology enhanced for repetitive avalanche

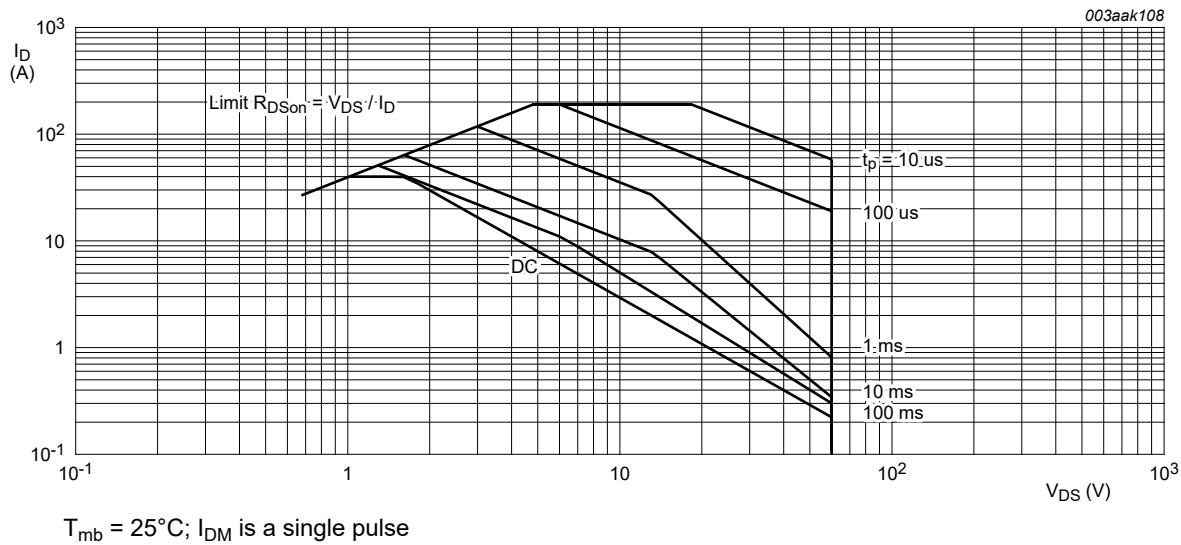


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

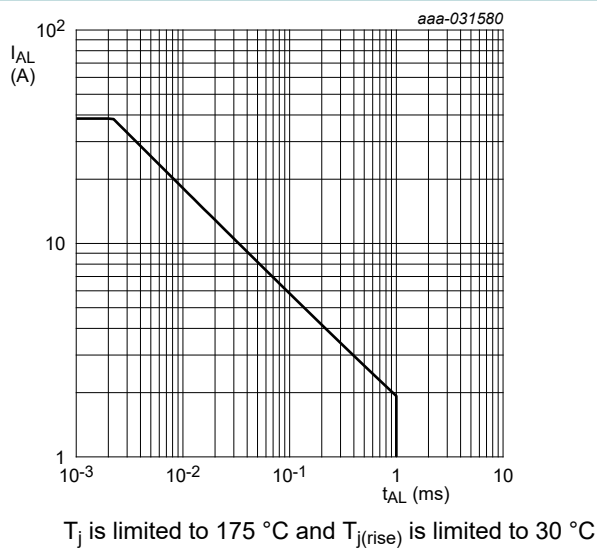


Fig. 4. Repetitive avalanche rating; avalanche current as a function of avalanche time

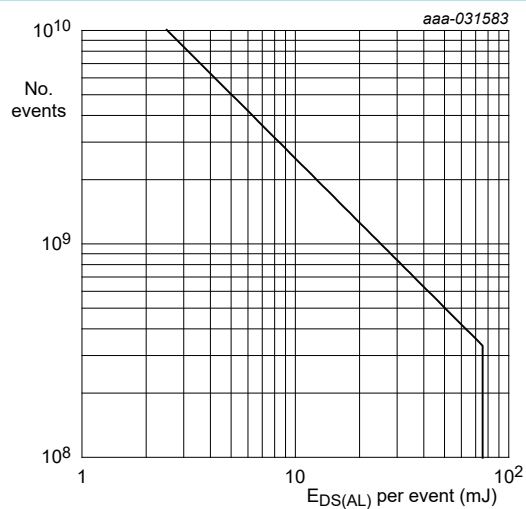


Fig. 5. Repetitive avalanche rating; maximum number of avalanche events as a function of avalanche energy

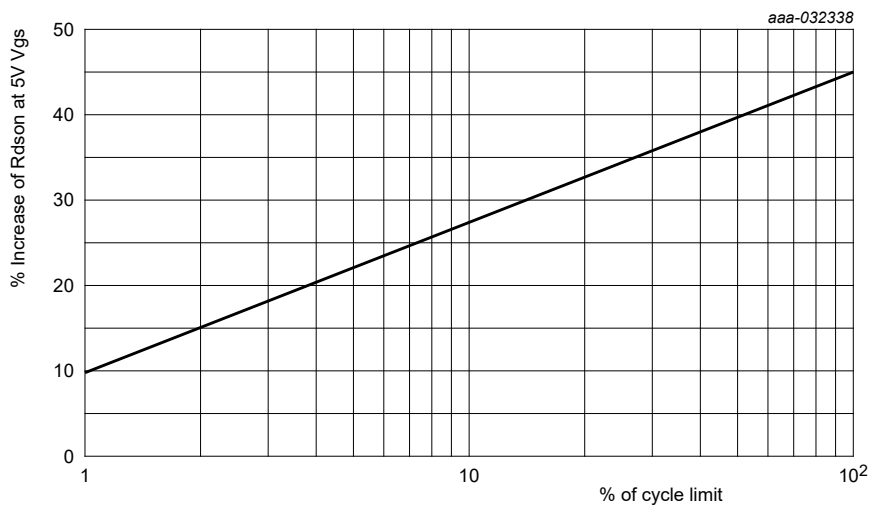
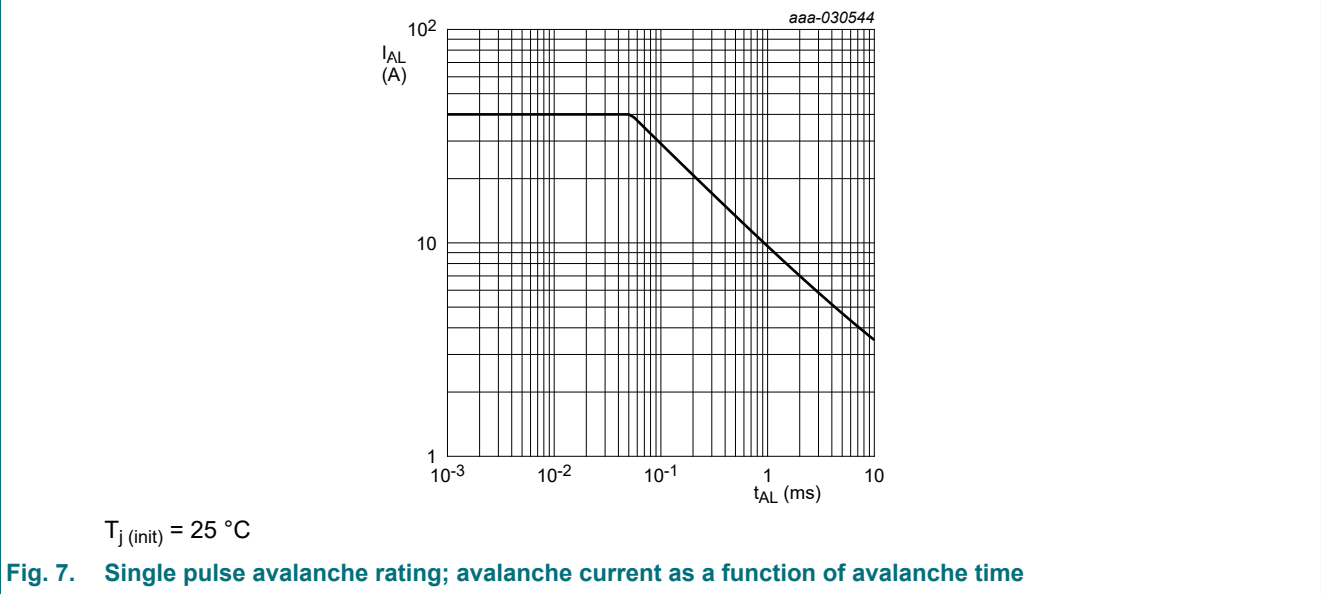


Fig. 6. Percentage $R_{DS(on)}$ at 5V increase as a function of avalanche cycles

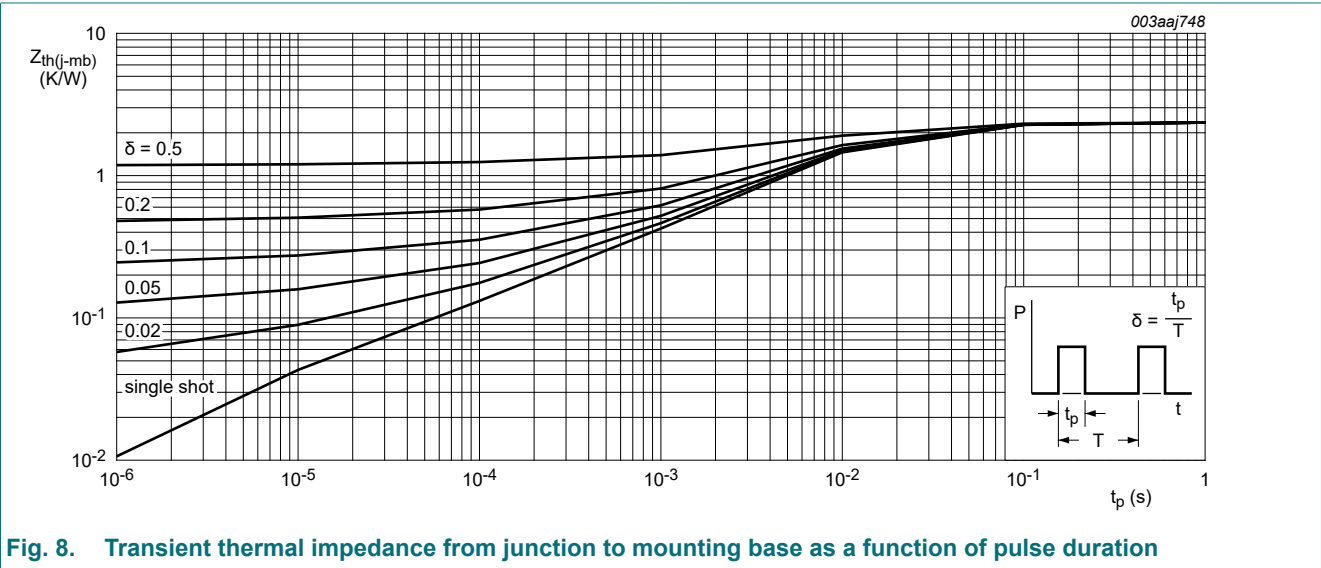
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 8	-	-	2.36	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics FET1 and FET2							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		54	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		60	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; Fig. 12 ; Fig. 13		1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 12		0.5	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; Fig. 12		-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C		-	0.02	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; Fig. 14		6.1	10	12.5	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 14 ; Fig. 15		-	22	28.3	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 14		5.4	9	11.2	mΩ
Dynamic characteristics FET1 and FET2							
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; Fig. 16 ; Fig. 17		-	22.4	-	nC
Q _{GS}	gate-source charge			-	5.2	-	nC
Q _{GD}	gate-drain charge			-	7.9	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 18		-	2215	2953	pF
C _{oss}	output capacitance			-	225	270	pF
C _{rss}	reverse transfer capacitance			-	116	159	pF
t _{d(on)}	turn-on delay time	V _{DS} = 48 V; R _L = 5 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	13	-	ns
t _r	rise time			-	22.1	-	ns
t _{d(off)}	turn-off delay time			-	30.5	-	ns
t _f	fall time			-	21.8	-	ns
Source-drain diode FET1 and FET2							
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 19		-	0.78	1.2	V
t _{rr}	reverse recovery time	I _S = 10 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 30 V; T _j = 25 °C		-	22.7	-	ns
Q _r	recovered charge			-	18.9	-	nC

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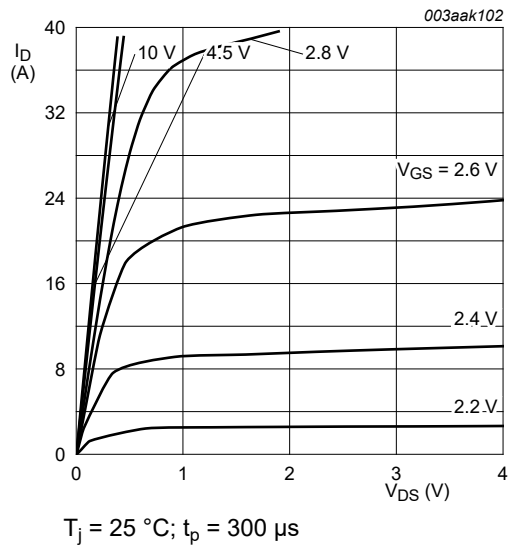


Fig. 9. Output characteristics; drain current as a function of drain-source voltage; typical values

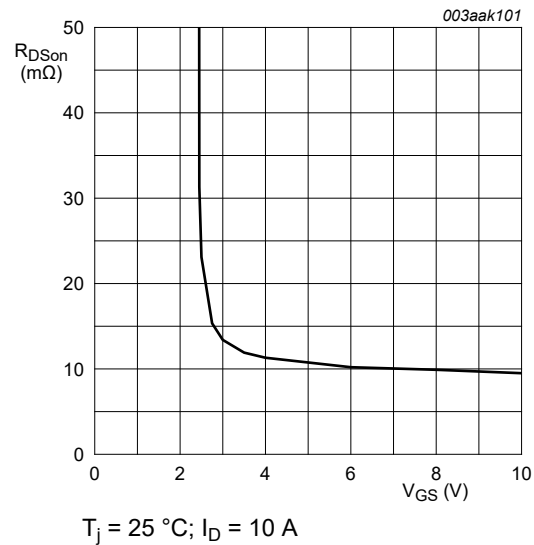


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

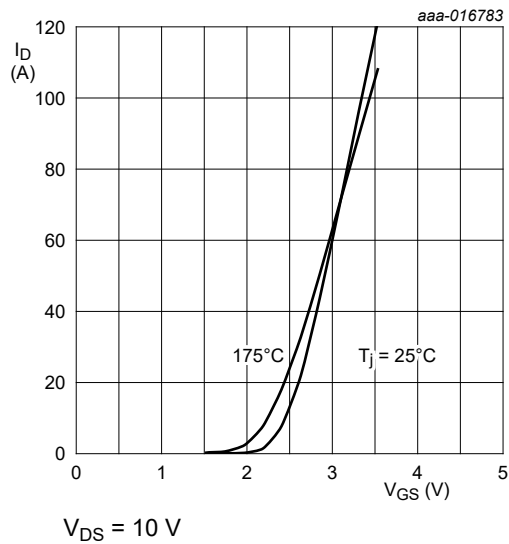


Fig. 11. Transfer characteristics; drain current as a function of gate-source voltage; typical values

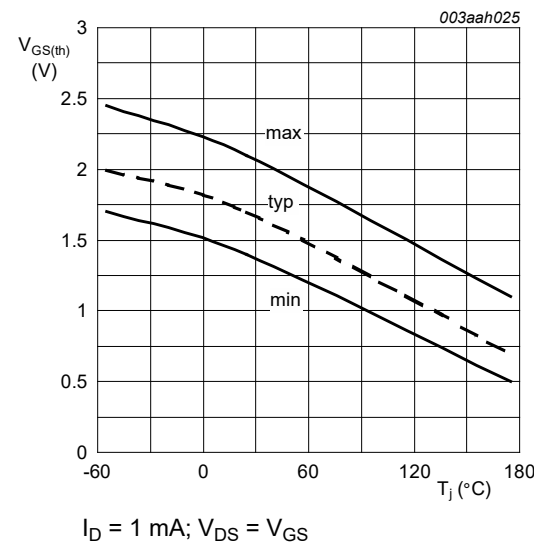


Fig. 12. Gate-source threshold voltage as a function of junction temperature

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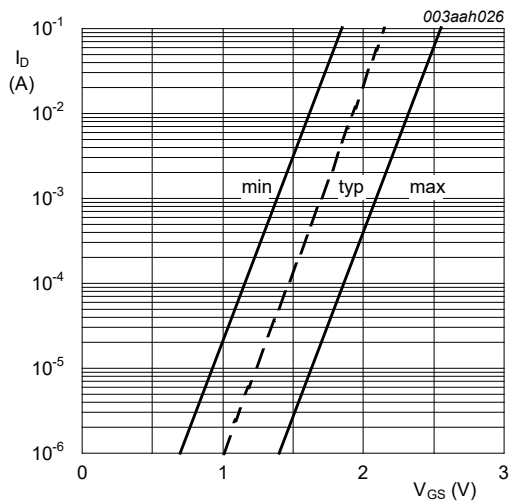


Fig. 13. Sub-threshold drain current as a function of gate-source voltage

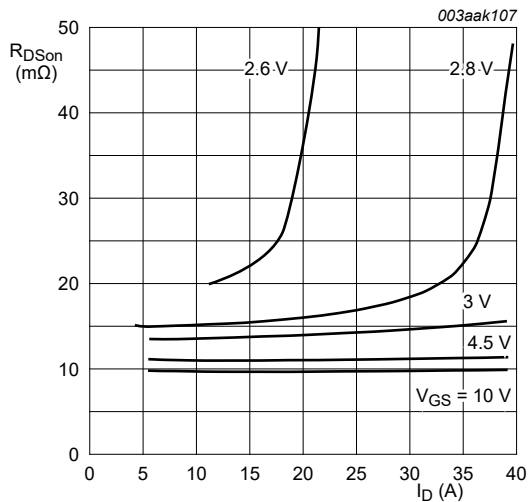


Fig. 14. Drain-source on-state resistance as a function of drain current; typical values

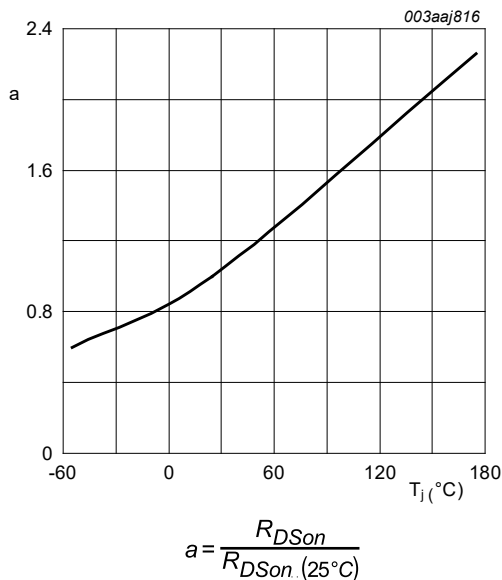


Fig. 15. Normalized drain-source on-state resistance factor as a function of junction temperature

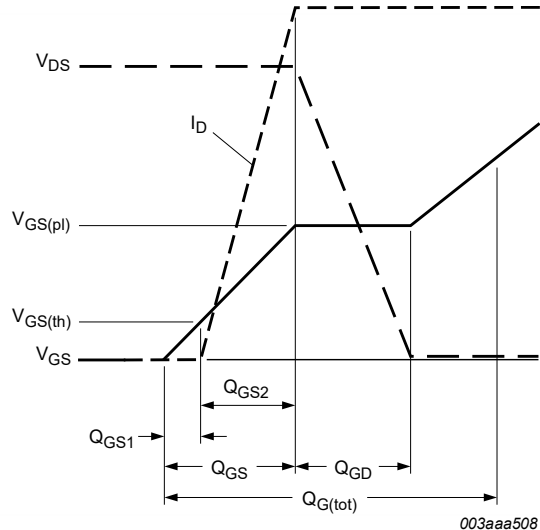


Fig. 16. Gate charge waveform definitions

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LPAK56D using TrenchMOS technology enhanced for repetitive avalanche

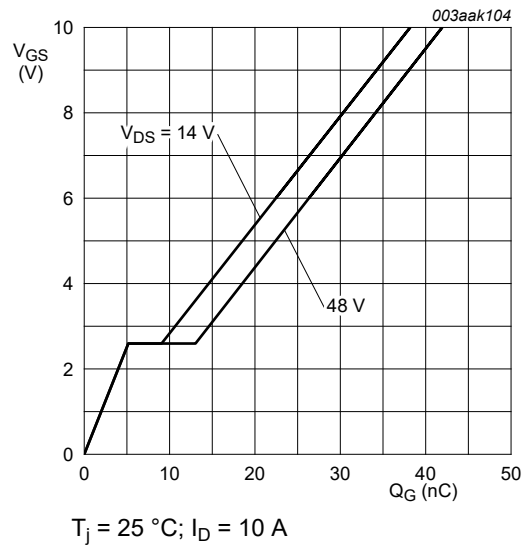


Fig. 17. Gate-source voltage as a function of gate charge; typical values

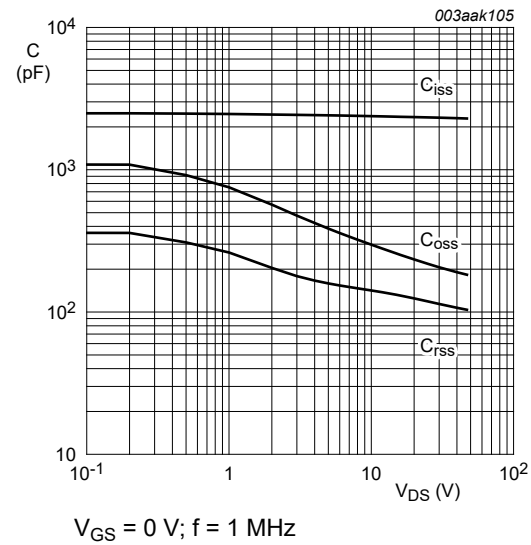


Fig. 18. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

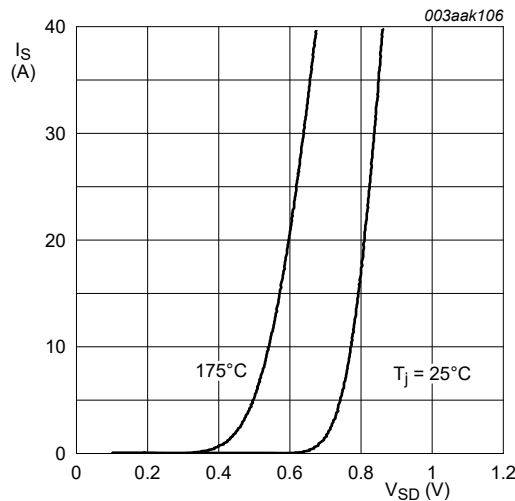


Fig. 19. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

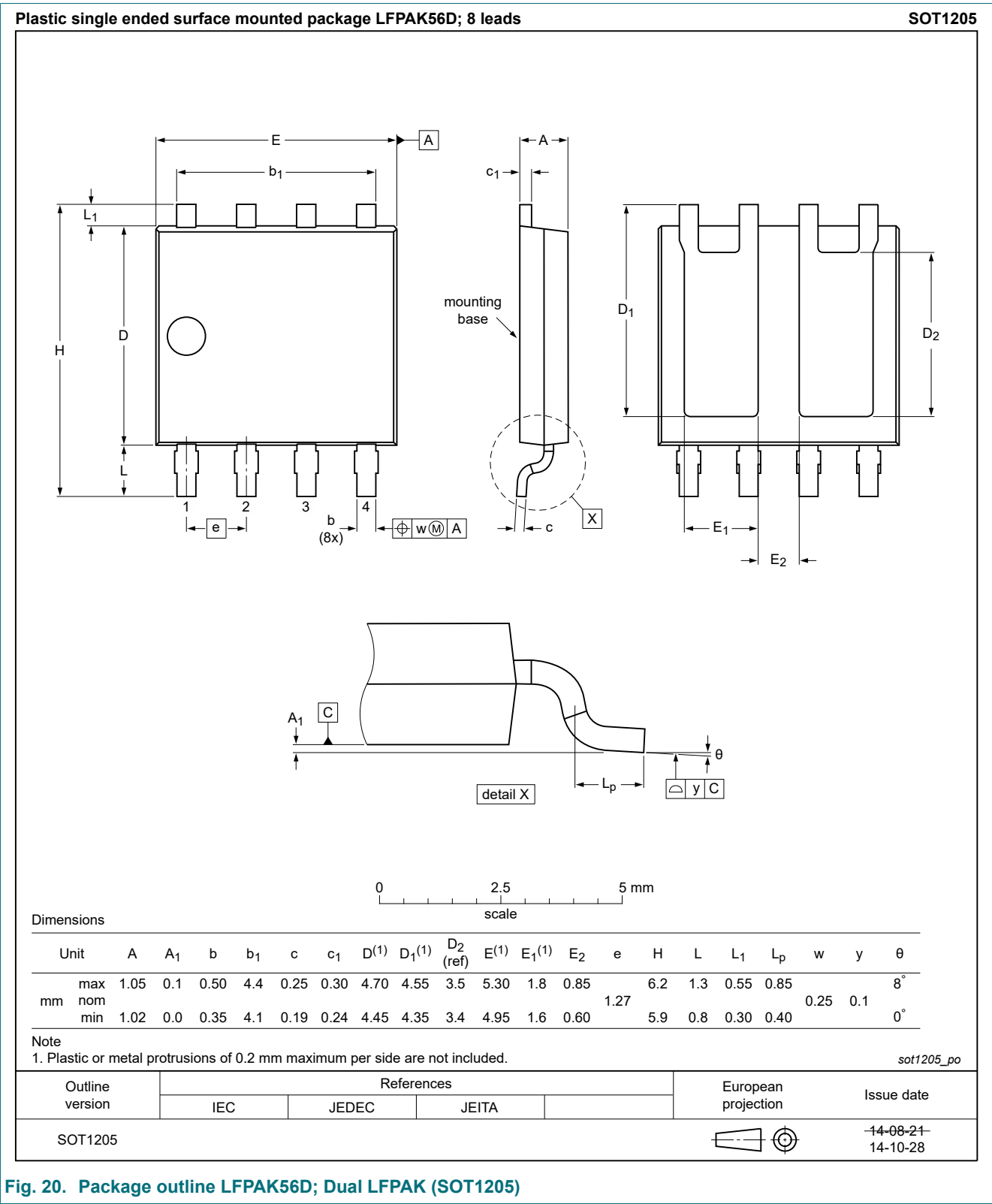


Fig. 20. Package outline LPAK56D; Dual LPAK (SOT1205)

12. Soldering

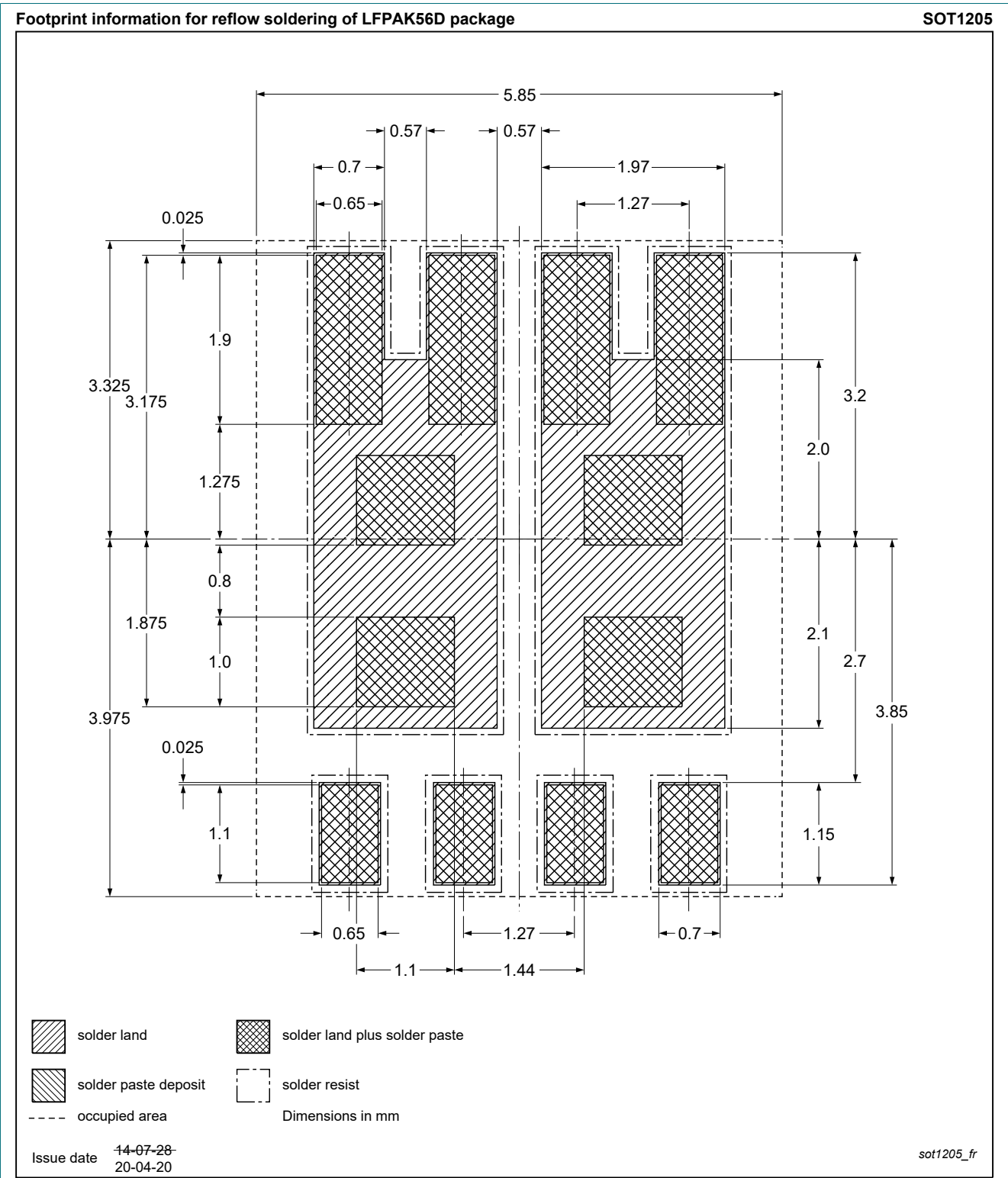


Fig. 21. Reflow soldering footprint for LPAK56D; Dual LPAK (SOT1205)

N-channel 60 V, 12.5 mOhm, logic level MOSFET in LPAK56D using TrenchMOS technology enhanced for repetitive avalanche

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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